

INFORMATION DISCLOSURE STATEMENT <i>(Use Several Sheets if necessary)</i>		ATTY DOCKET NO.		APPLICATION NO.		
		UTC 003		90/523,491		
		APPLICANT		Klaus et al.		
		FILING DATE		GROUP		
March 10, 2000		2811				
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS						
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OTHER DISCLOSURES (Including Author, Title, Date, Pertinent Pages, Place of Publication, Etc.)						
EF	Kumagai et al., FABRICATION OF TITANIUM OXIDE THIN FILMS..., 1995, Thin Solid Films 263, pgs. 47-53					
EF	Ritala et al., STUDIES ON THE MORPHOLOGY OF Al ₂ O ₃ THIN FILMS..., 1996, Thin Solid Films 286, pgs. 54-58					
EF	Ritala et al., GROWTH OF TITANIUM DIOXIDE THIN FILMS..., 1993, Thin Solid Films 225, pgs. 288-295					
EF	Han et al., A NEAR-EDGE X-RAY ABSORPTION FINE STRUCTURE STUDY OF ATOMIC LAYER EPITAXY..., 1998, Surface Science 415, pgs. 251-263					
EF	Morishita et al., ATOMIC-LAYER CHEMICAL-VAPOR-DEPOSITION OF SILICON-NITRATE, 1997, Applied Surface Science 112, pgs. 198-204					
EF	Takahashi et al., GERMANIUM ATOMIC LAYER EPITAXY CONTROLLED BY SURFACE CHEMICAL REACTIONS, June 1989, Journal of Electrochem. Soc.-Vol. 136-No. 6, pgs. 1826-1827					
EF	Gates et al., EPITAXIAL Si FILMS ON Ge(100) GROWN VIA H/Cl EXCHANGE, Feb. 1993, Applied Phys. Lett. 62 (5), pgs. 510-512					
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EF	Juppo et al., DEPOSITION OF COPPER FILMS BY AN ALTERNATE SUPPLY OF CuCl AND Zn, 1997, Journal of Vac. Sci. Technol. A 15(4), pgs. 2330-2333					
EF	Bell et al., BATCH REACTOR KINETIC STUDIES OF TUNGSTEN LPCVD..., Jan. 1996, Journal of Electrochem. Soc.- Vol. 143-No.1, pgs. 296-302					
EF	Martensson et al., ATOMIC LAYER EPITAXY OF COPPER ON TANTALUM, 1997, Chem. Vap. Deposition-3-No. 1, pgs. 1-6					
EF	Kumagai et al., TITANIUM OXIDE/ALUMINUM OXIDE MULTILAYER REFLECTORS..., May 1997, Applied Phys. Lett. 70 (18), pgs. 2338-2340					
EXAMINER	<i>[Signature]</i>		DATE CONSIDERED			11/12/02
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EF	Kobayashi et al., STUDY ON MECHANISM OF SELECTIVE CHEMICAL VAPOR DEPOSITION..., Jan. 1991, Journal of appl. Phys. 69 (2), pgs. 1013-1019					
EF	Klaus et al., ATOMIC LAYER CONTROLLED GROWTH OF SiO ₂ FILMS..., March 1997, Applied Phys. Lett. 70 (9), pgs. 1092-1094					
EF	Klaus et al., Al ₂ O ₃ THIN FILM GROWTH ON Si(100) USING BINARY REACTION SEQUENCE CHEMISTRY, 1997, Thin Solid Films 292, pgs. 135-144					
EF	George et al., SURFACE CHEMISTRY FOR ATOMIC LAYER GROWTH, 1996, Journal of Phys. Chem 100, pgs. 13121-13131					
EF	Klaus et al., ATOMIC LAYER CONTROLLED GROWTH OF Si ₃ N ₄ FILMS..., 1998, Surface Science 418, pgs. L14-L19					
EXAMINER	<i>G. Smith</i>		DATE CONSIDERED <i>11/12/02</i>			
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